EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S33	20	(US-20020094686-$ or US-20030118731-$ or US-20040135217-$ or US-20040048491-$ or US-20040129294-$ or US-20040118805-$ or US-20040026374-$ or US-20040089536-$ or US-20050215059-$ or US-20020096512-$).did. or (US-6565667-$ or US-6613603-$ or US-4842897-$ or US-6063142-$ or US-6812101-$ or US-6787440-$ or US-6465371-$ or US-6861101-$).did. or (JP-2003203906-$ or JP-05092165-$).did. or (US-20030129772-A-$).did.	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/11/10 15:46
S34	389100	S33 and (silicon) or (silicon near2 $2oxide$2)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/10 15:48
S35	13	S33 and ((silicon) or (silicon near2 $2oxide$2))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/10 15:48
S36	2	("2002/0094686").URPN.	USPAT	ADJ	ON	2008/11/10 16:08
S37	1	("20060170740").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/11/12 08:01
S38	11695	semiconductor$2 and (silicon with dielectric)	EPO; JPO; DERWENT	ADJ	ON	2008/11/12 08:51
S39	13	semiconductor$2 and (silicon with dielectric) and (micro near2 (fissur$3 or crack$3 or trench$3 or via $2))	EPO; JPO; DERWENT	ADJ	ON	2008/11/12 08:54
S40	1	("1158072").PN.	EPO	OR	OFF	2008/11/12 09:08

S41	2	("6783875").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/12 09:14
S44	4123	semiconductor$2 and ((("si" or silicon) same ("yt" or yttrium) same oxide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/12 09:24
S45	38	semiconductor$2 and ((("si" or silicon) same ("yt" or yttrium) same oxide) same (rough$4 with surface)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/12 09:25
S46	37	semiconductor$2 and ((("si" or silicon or "sio. sub."$) same ("yt" or yttrium or "yto.sub."$) same $2oxide) same (rough$4 with surface)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/12 10:19
S47	94	semiconductor$2 and ((("si" or silicon) same ("y" or yttrium) same $2oxide) same (rough$4 with surface)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/12 10:25
S48	95	semiconductor$2 and ((("si" or silicon) same ("y" or yttrium) same $2oxide) same ((rough$4 with surface) or (micro near2 (crack$4 or fissur$3 or trench$2 or via$2)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/12 10:26

11/12/2008 3:46:19 PM
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